Doc code :IDS Doc description: Information Disclosure Statement (IDS) Filed

PTO/SB/08a (09-08)
Approved for use through 10/31/2008. OMB 0651-0031
Ormation Disclosure Statement (IDS) Filed
U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE
Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

	Application Number		10715628	
INFORMATION DISCLOSURE	Filing Date		2003-11-17	
	First Named Inventor Garo J		J. Derderian	
(Not for submission under 37 CFR 1.99)	Art Unit		1792	
(Not for Submission under 57 Of K 1.33)	Examiner Name	Zervig	gon, Rudy	
	Attorney Docket Numb	er	MI22-2427	

	U.S.PATENTS					Remove
Examiner Initial*	Cite No	Patent Number	Kind Code ¹	Issue Date	Name of Patentee or Applicant of cited Document	Pages,Columns,Lines where Relevant Passages or Relevant Figures Appear
	1	4444812		1984-04-24	Gutsche	
	2	4545327		1985-10-08	Campbell et al.	
	3	4592933		1986-06-03	Meyerson et al.	
	4	4724159		1988-02-09	Yamazaki	
	5	4761269		1988-08-02	Conger et al.	
	6	4798809		1989-01-17	Hirooka et al.	
	7	4904621		1990-02-27	Loewenstein et al.	
	8	4910043		1990-03-20	Freeman et al.	

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Not for submission under 37 CFR 1.99)

Application Number		10715628	
Filing Date		2003-11-17	
First Named Inventor Garo		J. Derderian	
Art Unit		1792	
Examiner Name	Zervig	gon, Rudy	
Attorney Docket Number		MI22-2427	

9	4949669	1990-08-21	Ishii et al.	
10	4965090	1990-10-23	Gartner et al.	
11	4971832	1990-11-20	Arai et al.	
12	5068871	1991-11-26	Uchida et al.	
13	5077875	1992-01-07	Hoke et al.	
14	5093149	1992-03-03	Doehler et al.	
15	5618349	1997-04-08	Yuuki	
16	5674574	1997-10-07	Atwell et al.	
17	5925411	1999-07-20	van de Ven et al.	
18	5993916	1999-11-30	Zhao et al.	
19	6110531	2000-08-29	Paz de Araujo et al.	

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Not for submission under 37 CFR 1.99)

Application Number		10715628	
Filing Date		2003-11-17	
First Named Inventor	Garo	J. Derderian	
Art Unit		1792	
Examiner Name	Zervig	gon, Rudy	
Attorney Docket Number		MI22-2427	

	20	6344151	B1	2002-02	!-05	Chen et al.					
	21	6638880	B2	2003-10-28		Yamamuka et	al.				
	22	6812157	B1	2004-11-02		Gadgil					
	23	7066194	B2	2006-06-27 I		Ku et al.					
If you wis	h to ac	dd additional U.S. Pater	t citatio	n inform	ation pl	ease click the	Add button.		Add		
			U.S.P	ATENT	APPLI	CATION PUBI	LICATIONS		Remove		
Examiner Initial*	Cite No	Publication Number	Kind Code ¹	Publication Date		Name of Patentee or Applicant of cited Document		Relev	s,Columns,Line ant Passages o es Appear		
	1	20030194861	A1	2003-10-16 Mardian et al.		Mardian et al.					
If you wis	h to ac	dd additional U.S. Publis	hed Ap	plication	citation	n information p	lease click the Add	d butto	n. Add		
				FOREIC	SN PAT	ENT DOCUM	ENTS		Remove		
Examiner Initial*	Cite No	Foreign Document Number ³	Country Kind Code ² i Code ⁴			Publication Date	Name of Patentee or Applicant of cited Document		Pages,Column where Relevan Passages or Re Figures Appear	t elevant	T5
	1	2000079019	WO	A1		2000-12-28	Gadgil				
	2	2003076678	WO	A2		2003-09-18	Sundew Technolog LLC	ies,			
If you wis	h to ac	dd additional Foreign Pa	tent Do	cument	citation	information pl	ease click the Add	button	Add		
NON-PATENT LITERATURE DOCUMENTS								Remove			

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Not for submission under 37 CFR 1.99)

Application Number		10715628
Filing Date		2003-11-17
First Named Inventor Garo		J. Derderian
Art Unit		1792
Examiner Name	Zervig	gon, Rudy
Attorney Docket Number		MI22-2427

Examiner Initials*	Cite No	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, pages(s), volume-issue number(s), publisher, city and/or country where published.							
	1	HORII, Sadayoshi, et al., "Metalorganic Chemical Vapor Deposition of HfO2 Films through the Alternating Supply of Tetrakis(1-methoxy-2-methyl-2-propoxy)-Hafnium and Remote-Plasma Oxygen". Jpn. J. Appl. Phys. Vol. 42 (2003), pp. 5176-5180, Part 1, No. 8, 15 August 2003.							
	2		SUNDQVIST, J., et al., "Atomic layer deposition of polycrystalline HfO2 films by the Hfl4-O2 precursor combination". Thin Solid Films. Volume 427, Issues 1-2, 3 March 2003, pp. 147-151.						
If you wis	h to ac	dd addi	litional non-patent literature document citation information p	lease click the Add I	outton Add				
			EXAMINER SIGNATURE						
Examiner	Signa	ture		Date Considered					
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through a citation if not in conformance and not considered. Include copy of this form with next communication to applicant.									
¹ See Kind Codes of USPTO Patent Documents at <u>www.USPTO.GOV</u> or MPEP 901.04. ² Enter office that issued the document, by the two-letter code (WIPO Standard ST.3). ³ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁴ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁵ Applicant is to place a check mark here if English language translation is attached.									